

KA1M0265R/KA1H0265R

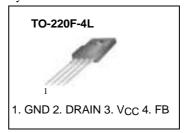
Fairchild Power Switch(FPS)

Features

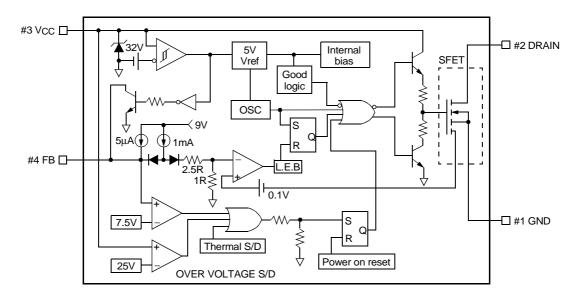
- Precision Fixed Operating Frequency
- KA1M0265R (70kHz), KA1H0265R (100kHz)
- Pulse by Pulse Over Current Limiting
- Over Load Protection
- Over Voltage Protection (Min. 23V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- · Internal High Voltage Sense FET
- · Auto Restart

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit. compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a forward converter.



Internal Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Maximum Drain Voltage (1)	V _D ,MAX	650	V
Drain-Gate Voltage (RGS=1MΩ)	VDGR	650	V
Gate-Source (GND) Voltage	Vgs	±30	V
Drain Current Pulsed (2)	IDM	8.0	ADC
Single Pulsed Avalanche Energy (3)	Eas	68	mJ
Continuous Drain Current (T _C =25°C)	ΙD	2.0	ADC
Continuous Drain Current (Tc=100°C)	ID	1.3	ADC
Maximum Supply Voltage	VCC,MAX	30	V
Input Voltage Range	VFB	-0.3 to VSD	V
Total Dawer Dissipation	PD	42	W
Total Power Dissipation	Darting	0.33	W/°C
Operating Ambient Temperature	TA	-25 to +85	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes:

- 1. $T_j = 25^{\circ}C$ to $150^{\circ}C$
- 2. Repetitive rating: Pulse width limited by maximum junction temperature
- 3. L = 51mH, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25°C

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	Vgs=0V, ID=50μA	650	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	VDS=Max., Rating, VGS=0V	-	-	50	μА
		V _{DS} =0.8Max., Rating, V _{GS} =0V, T _C =125°C	-	-	200	μА
Static Drain-Source on Resistance (Note)	RDS(ON)	VGS=10V, ID=1.0A	-	5.0	6.0	Ω
Forward Transconductance (Note)	gfs	V _{DS} =50V, I _D =1.0A	1.5	2.5	-	S
Input Capacitance	Ciss		-	550	-	
Output Capacitance	Coss	VGS=0V, VDS=25V, f=1MHz	-	38	-	рF
Reverse Transfer Capacitance	Crss	1-11/11/2	-	17	-	
Turn on Delay Time	td(on)	VDD=0.5BVDSS, ID=2.0A (MOSFET switching time are essentially independent of operating temperature)	-	20	-	
Rise Time	tr		-	15	-	nS
Turn Off Delay Time	td(off)		-	55	-	113
Fall Time	tf		-	25	-	
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	VGS=10V, ID=2.0A, VDS=0.5BVDSS (MOSFET switching time are essentially independent of operating temperature)	-	-	35	
Gate-Source Charge	Qgs		-	3	-	nC
Gate Drain (Miller) Charge	Qgd		-	12	-	

Note:

1. Pulse test: Pulse width $\leq 300 \mu S$, duty cycle $\leq 2\%$ 2. $S = \frac{1}{R}$

2. S =
$$\frac{1}{R}$$

Electrical Characteristics (Control Part) (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
UVLO SECTION						1
Start Threshold Voltage	VSTART	-	14	15	16	V
Stop Threshold Voltage	VSTOP	After turn on	9	10	11	V
OSCILLATOR SECTION						
Initial Accuracy	Fosc	KA1M0265R	61	67	73	- kHz
		KA1H0265R	90	100	110	
Frequency Change With Temperature (2)	ΔΕ/ΔΤ	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%
Maximum Duty Cycle	Descri	KA1M0265R	74	77	80	%
	Dmax	KA1H0265R	64	67	70	
FEEDBACK SECTION				•		
Feedback Source Current	IFB	Ta=25°C, 0V ≤ Vfb ≤ 3V	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	VsD	-	6.9	7.5	8.1	V
Shutdown Delay Current	Idelay	Ta=25°C, 5V ≤ Vfb ≤ VsD	4.0	5.0	6.0	μΑ
REFERENCE SECTION						
Output Voltage (1)	Vref	Ta=25°C	4.80	5.00	5.20	V
Temperature Stability (1)(2)	Vref/∆T	-25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C
CURRENT LIMIT (SELF-PROTECTION)	SECTION					•
Peak Current Limit	IOVER	Max. inductor current	1.05	1.2	1.35	Α
PROTECTION SECTION						•
Thermal Shutdown Temperature (Tj) (1)	T _{SD}	-	140	160	-	°C
Over Voltage Protection Voltage	Vovp	-	23	25	28	V
TOTAL DEVICE SECTION						1
Start-Up Current	ISTART	VCC=14V	0.1	0.3	0.4	mA
Operating Supply Current (Control Part Only)	lop	Ta=25°C	6	12	18	mA
VCC Zener Voltage	Vz	ICC=20mA	30	32.5	35	V

Note:

^{1.} These parameters, although guaranteed, are not 100% tested in production

^{2.} These parameters, although guaranteed, are tested in EDS (wafer test) process

Typical Performance Characteristics

(These characteristic graphs are normalized at Ta=25°C)

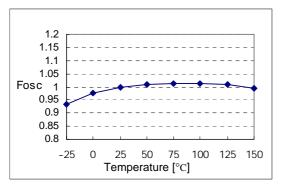


Figure 1. Operating Frequency

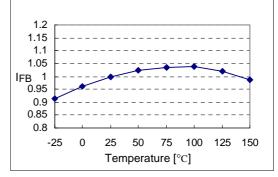


Figure 2. Feedback Source Current

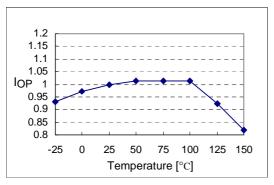


Figure 3. Operating Supply Current

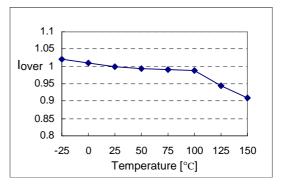


Figure 4. Peak Current Limit

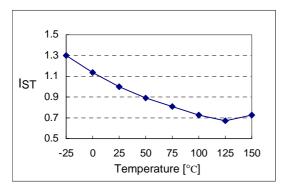


Figure 5. Start up Current

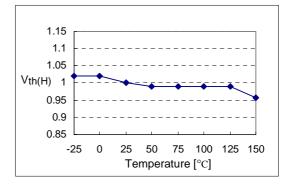


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at Ta=25°C)

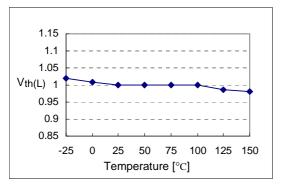


Figure 7. Stop Threshold Voltage

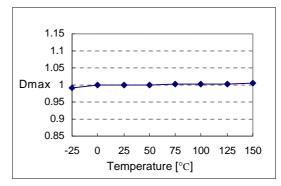


Figure 8. Maximum Duty Cycle

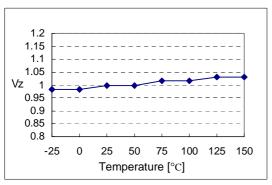


Figure 9. VCC Zener Voltage

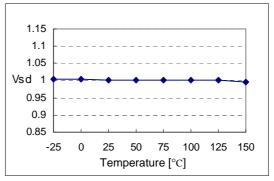


Figure 10. Shutdown Feedback Voltage

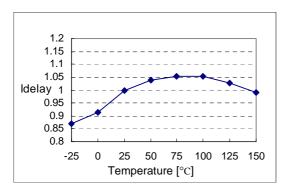


Figure 11. Shutdown Delay Current

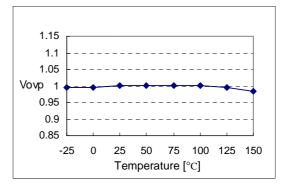


Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic groups are normalized at Ta=25°C)

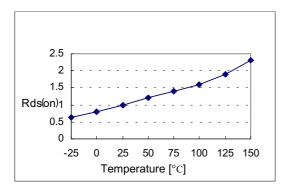
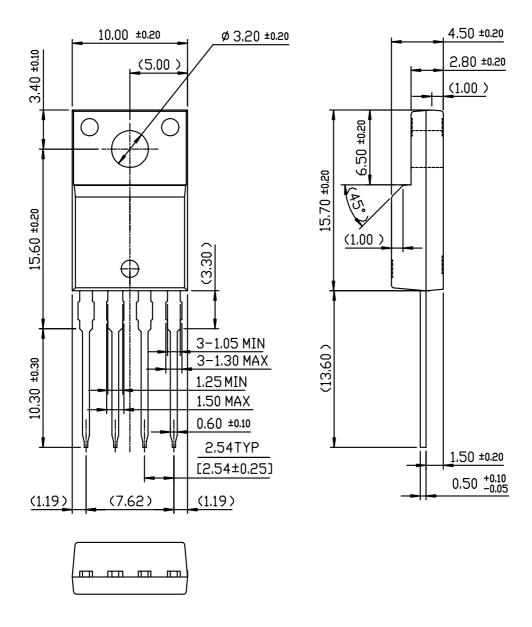


Figure 13. Static Drain-Source on Resistance

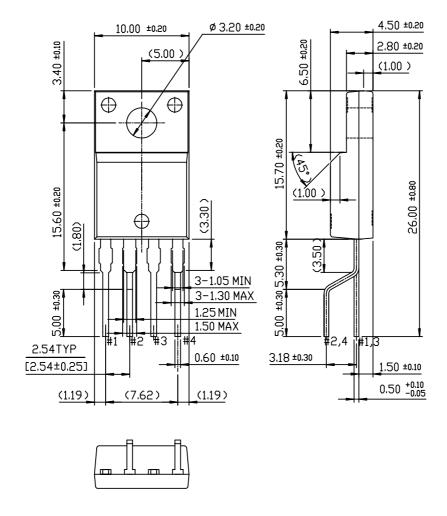
Package Dimensions

TO-220F-4L



Package Dimensions (Continued)

TO-220F-4L(Forming)



Ordering Information

Product Number	Package	Rating	Fosc		
KA1M0265R-TU	TO-220F-4L	650V, 2A	67kHz		
KA1M0265R-YDTU	TO-220F-4L(Forming)	030 V, ZA	O7 KHZ		
KA1H0265R-TU	TO-220F-4L	650V, 2A	100kHz		
KA1H0265R-YDTU	TO-220F-4L(Forming)	030 V, ZA	TOURHZ		

TU: Non Forming Type YDTU: Forming Type

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